

B170/B - B1100/B

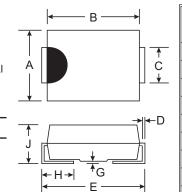
1.0A HIGH VOLTAGE SCHOTTKY BARRIER RECTIFIER

Features

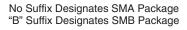
- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Ideally Suited for Automatic Assembly
- Low Power Loss, High Efficiency
- Surge Overload Rating to 30A Peak
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Application
- High Temperature Soldering: 260°C/10 Second at Terminal
- Lead Free Finish/RoHS Compliant (Note 3)

Mechanical Data

- Case: SMA / SMB
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Lead Free Plating (Matte Tin Finish). Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band or Cathode Notch
- Mounting Position: Any
- Marking: Type Number
- SMA Weight: 0.064 grams (approximate)
- SMB Weight: 0.093 grams (approximate)



Dim	SN	ΛA	SMB		
Dim	Min	Max	Min	Max	
Α	2.29	2.92	3.30	3.94	
В	4.00	4.60	4.06	4.57	
С	1.27	1.63	1.96	2.21	
D	0.15	0.31	0.15	0.31	
Е	4.80	5.59	5.00	5.59	
G	0.10 0.20		0.10	0.20	
Н	0.76	1.52	0.76	1.52	
J	2.01	2.30	2.00	2.40	
All Dimensions in mm					



Maximum Ratings and Electrical Characteristics @ T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic		Symbol	B170/B	B180/B	B190/B	B1100/B	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V _{RRM} V _{RWM} VR	70	80	90	100	V
RMS Reverse Voltage		V _{R(RMS)}	49	56	63	70	V
Average Rectified Output Current @ $T_T = 125^{\circ}C$		lo	1.0			Α	
Non-Repetitive Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)		I _{FSM}	30			А	
$\label{eq:Forward} \begin{array}{llllllllllllllllllllllllllllllllllll$		V _{FM}	0.79 0.69			V	
$ \begin{array}{c} \mbox{Peak Reverse Current} & @\ T_A = \ 25^\circ C \\ \mbox{at Rated DC Blocking Voltage} & @\ T_A = \ 100^\circ C \\ \end{array} $		I _{RM}	0.5 5.0				mA
Typical Junction Capacitance (Note 2)		Cj	80			pF	
Typical Thermal Resistance Junction to Terminal (Note 1)		R _{θJT}	25			K/W	
Operating and Storage Temperature Range		T _j , T _{STG}	-65 to +150			°C	

Notes: 1. Valid provided that terminals are kept at ambient temperature.

2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

3. RoHS revision 13.2.2003. Glass and High Temperature Solder Exemptions Applied, see EU Directive Annex Notes 5 and 7.



Ordering Information (Note 4)

Device*	Packaging	Shipping
B1x-13-F	SMA	5000/Tape & Reel
B1xB-13-F	SMB	3000/Tape & Reel

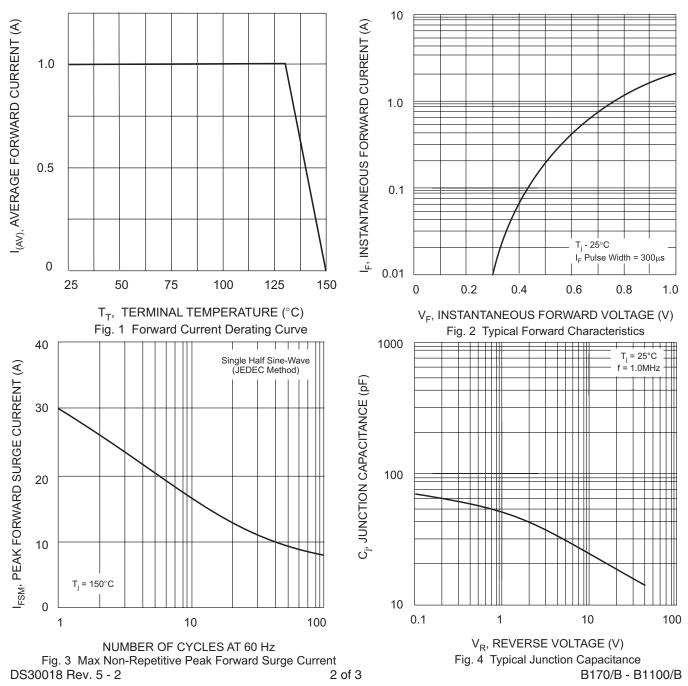
Notes: 4. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

* x = Device type, e.g. B180-13-F (SMA package); B1100B-13-F (SMB package).

Marking Information



XXX = Product type marking code, ex: B170 (SMA package) XXXX = Product type marking code, ex: B190B (SMB package)) | = Manufacturers' code marking YWW = Date code marking Y = Last digit of year ex: 2 for 2002 WW = Week code 01 to 52



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